

### General Description

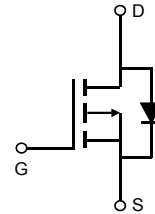
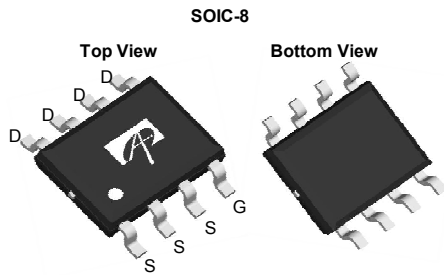
• The AO4413 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , and ultra-low low gate charge with a 25V gate rating. This device is suitable for use as a load switch or in PWM applications.

• RoHS and Halogen-Free Compliant

### Product Summary

$V_{DS}$	-30V
$I_D$ (at $V_{GS}=-20V$ )	-15A
$R_{DS(ON)}$ (at $V_{GS}=-20V$ )	< 7m $\Omega$
$R_{DS(ON)}$ (at $V_{GS} = -10V$ )	< 8.5m $\Omega$

100% UIS Tested  
 100%  $R_g$  Tested



### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 25$	V
Continuous Drain Current	$I_D$	$T_A=25^\circ\text{C}$	-15
		$T_A=70^\circ\text{C}$	-12.8
Pulsed Drain Current <sup>C</sup>	$I_{DM}$	-120	A
Avalanche Current <sup>C</sup>	$I_{AS}, I_{AR}$	50	A
Avalanche energy $L=0.1\text{mH}$ <sup>C</sup>	$E_{AS}, E_{AR}$	125	mJ
Power Dissipation <sup>B</sup>	$P_D$	$T_A=25^\circ\text{C}$	3.1
		$T_A=70^\circ\text{C}$	2
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	31	40	$^\circ\text{C/W}$
Maximum Junction-to-Ambient <sup>A,D</sup>		Steady-State	59	75
Maximum Junction-to-Lead	$R_{\theta JL}$	16	24	$^\circ\text{C/W}$

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =-250μA, V <sub>GS</sub> =0V	-30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			-1 -5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±25V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1.5	-2.5	-3.5	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-5V	-120			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-20V, I <sub>D</sub> =-15A T <sub>J</sub> =125°C		5.3 7.5	7 9	mΩ
		V <sub>GS</sub> =-10V, I <sub>D</sub> =-15A		6.4	8.5	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-15A		35		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V		-0.7	-1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				-4	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =-15V, f=1MHz	2310	2890	3500	pF
C <sub>oss</sub>	Output Capacitance		410	585	760	
C <sub>rss</sub>	Reverse Transfer Capacitance		280	470	660	
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	1.9	3.8	5.7	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, I <sub>D</sub> =-15A	40	51	61	nC
Q <sub>gs</sub>	Gate Source Charge		10	12	14	
Q <sub>gd</sub>	Gate Drain Charge		10	16	22	
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, R <sub>L</sub> =1.0Ω, R <sub>GEN</sub> =3Ω		16		ns
t <sub>r</sub>	Turn-On Rise Time			12		
t <sub>D(off)</sub>	Turn-Off DelayTime			45		
t <sub>f</sub>	Turn-Off Fall Time			22		
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =-15A, dI/dt=100A/μs	14	18	22	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =-15A, dI/dt=100A/μs	9	11	13	nC

A. The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150° C, using ≤ 10s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150° C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub>=25° C.

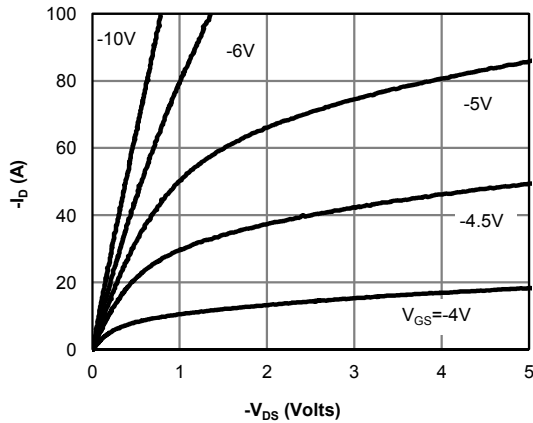
D. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

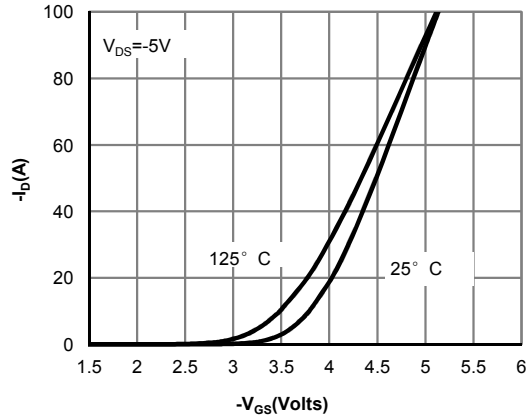
F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=150° C. The SOA curve provides a single pulse rating.

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

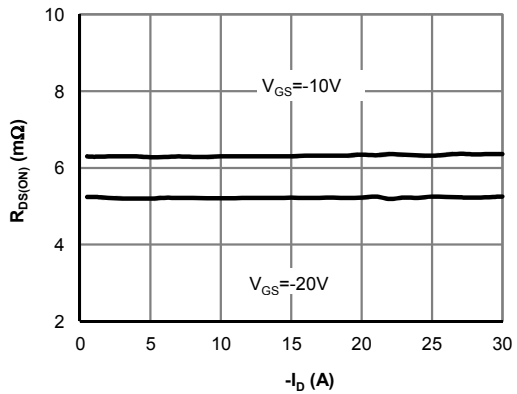
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



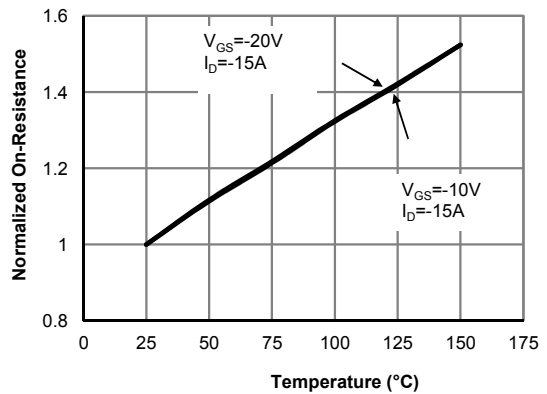
**Fig 1: On-Region Characteristics (Note E)**



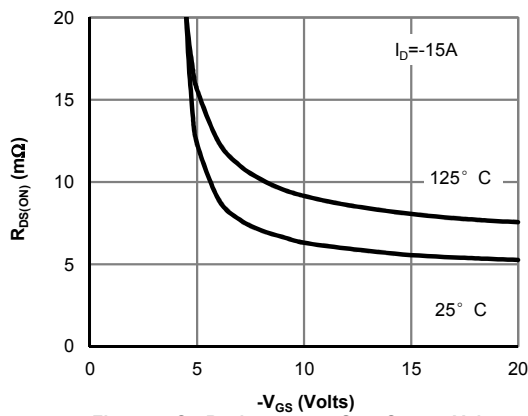
**Figure 2: Transfer Characteristics (Note E)**



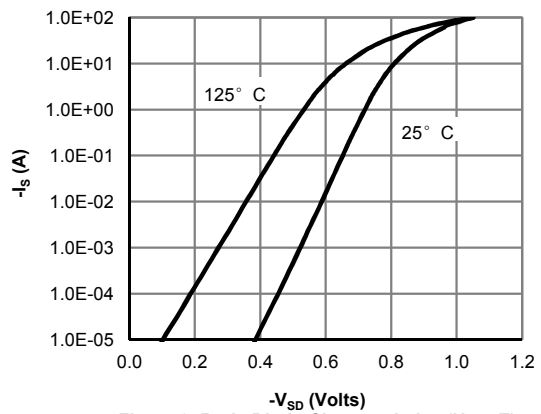
**Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)**



**Figure 4: On-Resistance vs. Junction Temperature (Note E)**

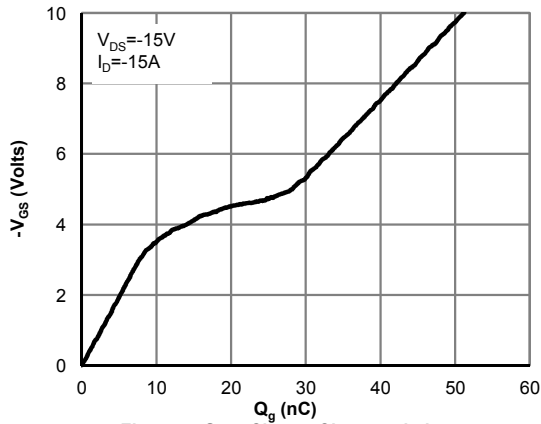


**Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)**

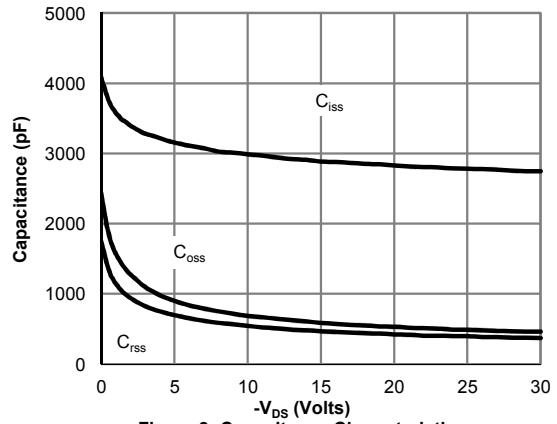


**Figure 6: Body-Diode Characteristics (Note E)**

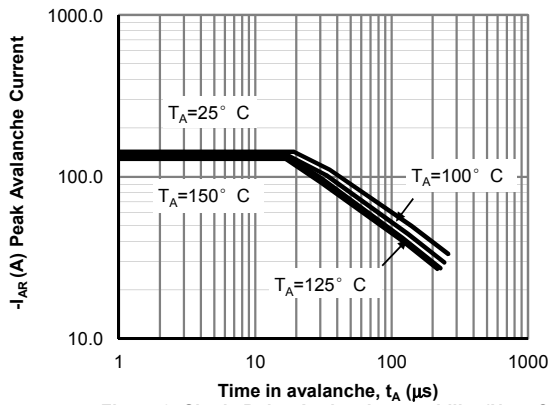
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



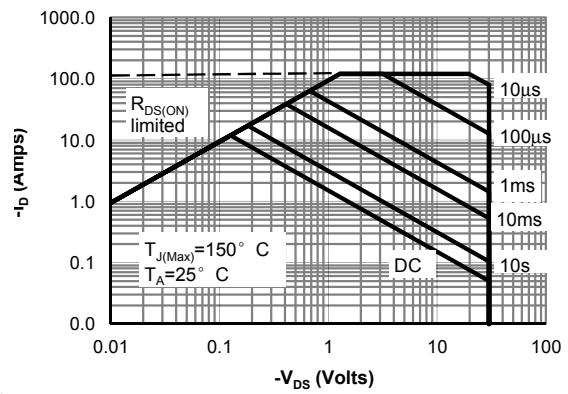
**Figure 7: Gate-Charge Characteristics**



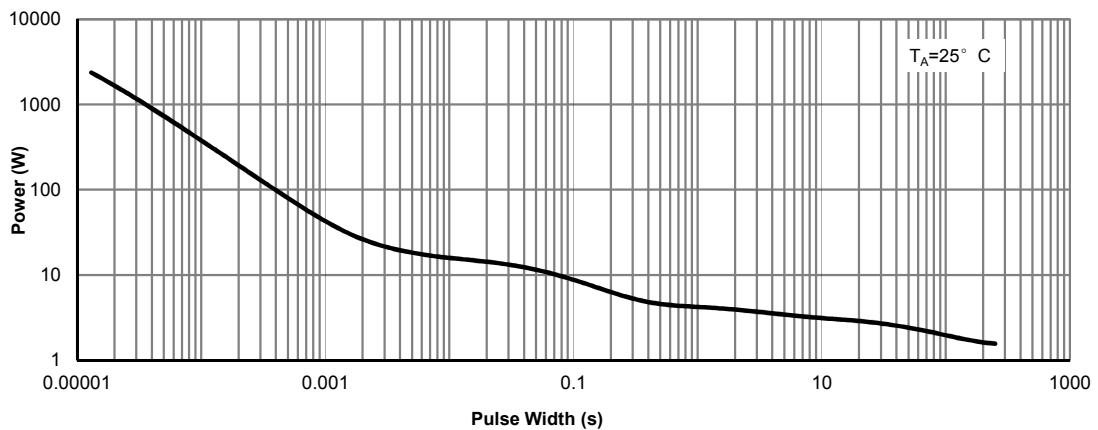
**Figure 8: Capacitance Characteristics**



**Figure 9: Single Pulse Avalanche capability (Note C)**

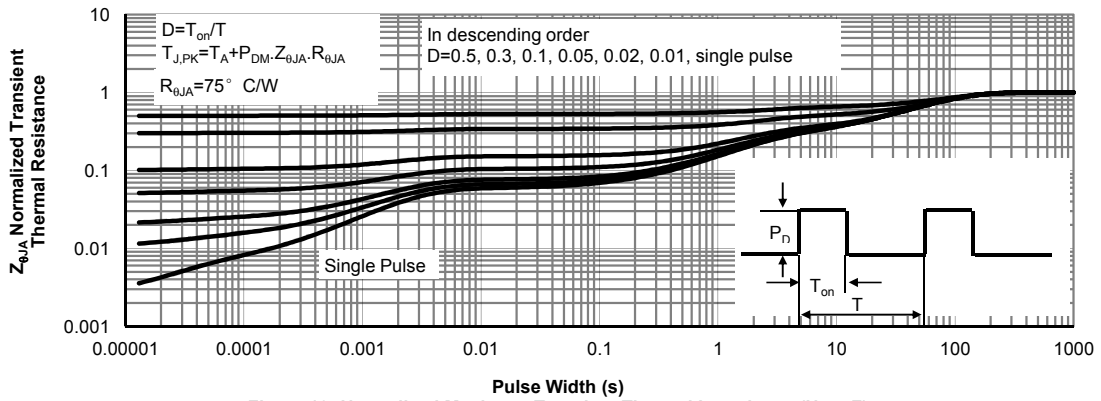


**Figure 10: Maximum Forward Biased Safe Operating Area (Note F)**



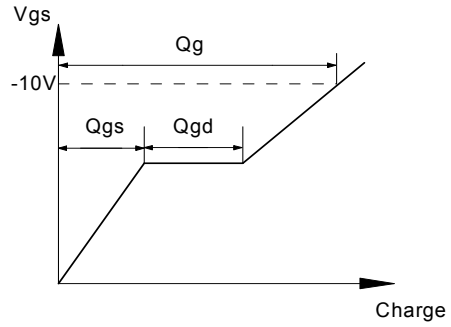
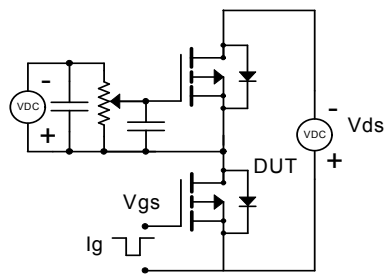
**Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note F)**

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

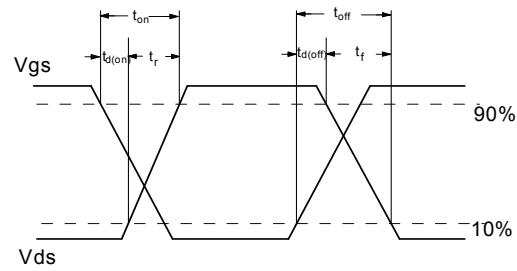
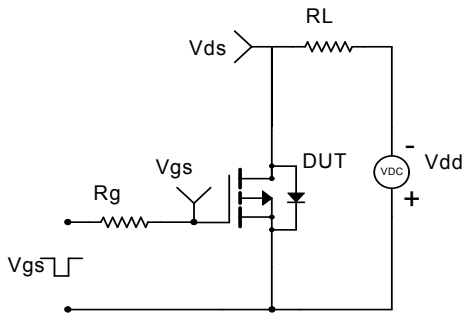


**Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)**

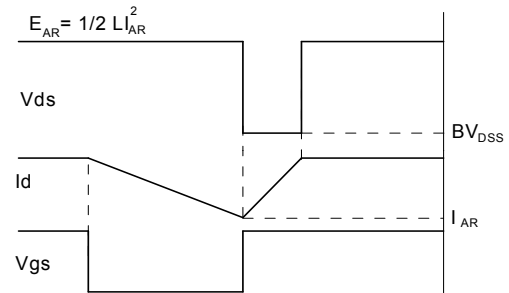
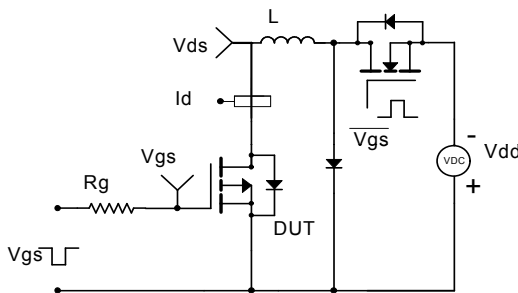
**Gate Charge Test Circuit & Waveform**



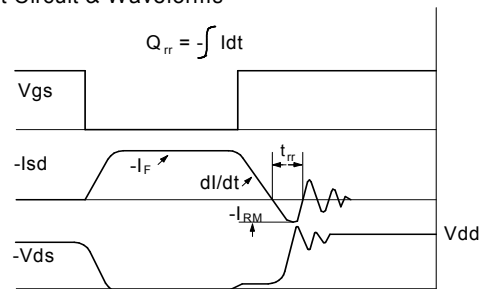
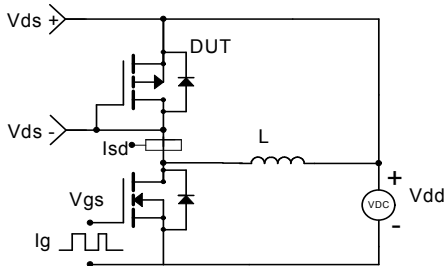
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching (UIS) Test Circuit & Waveforms**



**Diode Recovery Test Circuit & Waveforms**





Document No.	PD-00018
Version	F
Title	AO4413 Marking Description

SO-8 PACKAGE MARKING DESCRIPTION



Green product

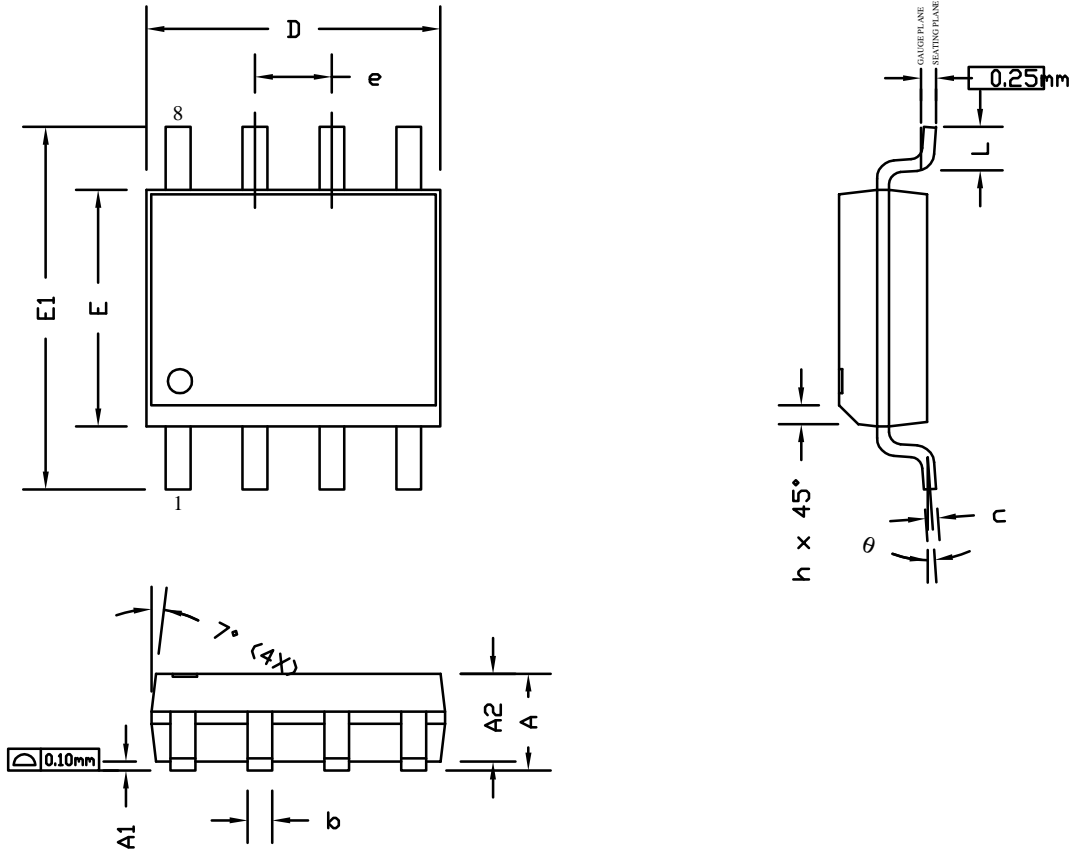
NOTE:	
LOGO	- AOS Logo
4413	- Part number code
F	- Fab code
A	- Assembly location code
Y	- Year code
W	- Week code
L&T	- Assembly lot code

PART NO.	DESCRIPTION	CODE
AO4413	Green product	4413
AO4413L	Green product	4413

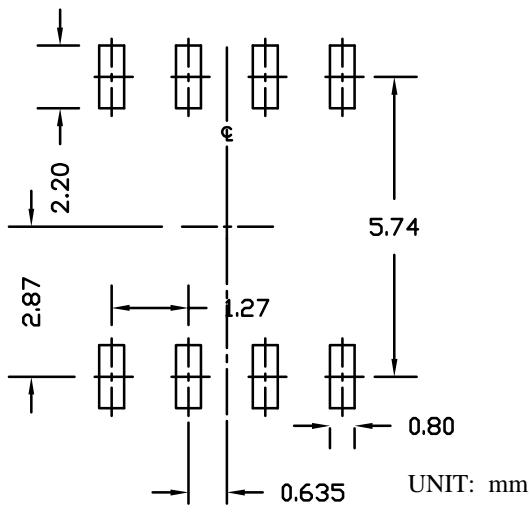


Document No.	PO-00004
Version	I

S08 PACKAGE OUTLINE



RECOMMENDED LAND PATTERN



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.35	1.65	1.75	0.053	0.065	0.069
A1	0.10	0.15	0.25	0.004	0.006	0.010
A2	1.25	1.50	1.65	0.049	0.059	0.065
b	0.31	0.41	0.51	0.012	0.016	0.020
c	0.17	0.20	0.25	0.007	0.008	0.010
D	4.80	4.90	5.00	0.189	0.193	0.197
E	3.80	3.90	4.00	0.150	0.154	0.157
e	1.27 BSC			0.050 BSC		
E1	5.80	6.00	6.20	0.228	0.236	0.244
h	0.25	0.30	0.50	0.010	0.012	0.020
L	0.40	0.69	1.27	0.016	0.027	0.050
θ	0°	4°	8°	0°	4°	8°

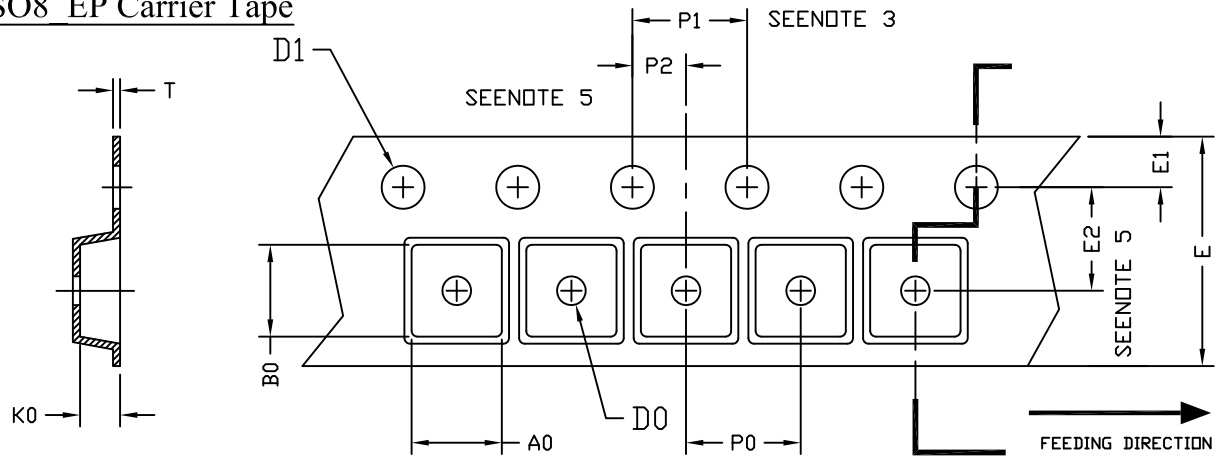
NOTE

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONS ARE INCLUSIVE OF PLATING.
3. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.  
MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
4. DIMENSION L IS MEASURED IN GAUGE PLANE.
5. CONTROLLING DIMENSION IS MILLIMETER.  
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.





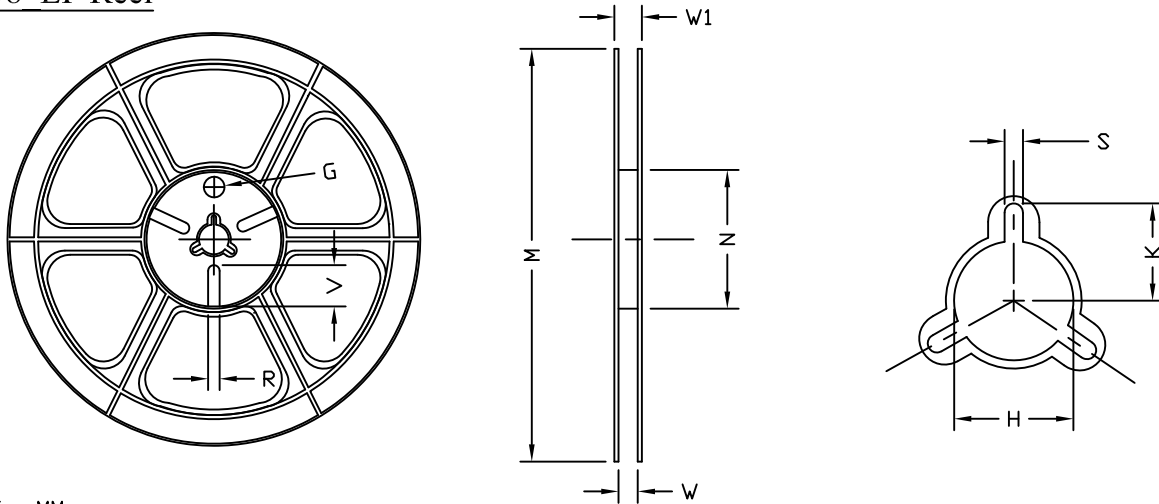
**SO8/SO8 EP Carrier Tape**



UNIT: MM

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SO-8 (12 mm)	6.40 ±0.10	5.20 ±0.10	2.10 ±0.10	1.60 ±0.10	1.50 +0.10	12.00 ±0.30	1.75 ±0.10	5.50 ±0.05	8.00 ±0.10	4.00 ±0.10	2.00 ±0.05	0.25 ±0.05

**SO8/SO8 EP Reel**



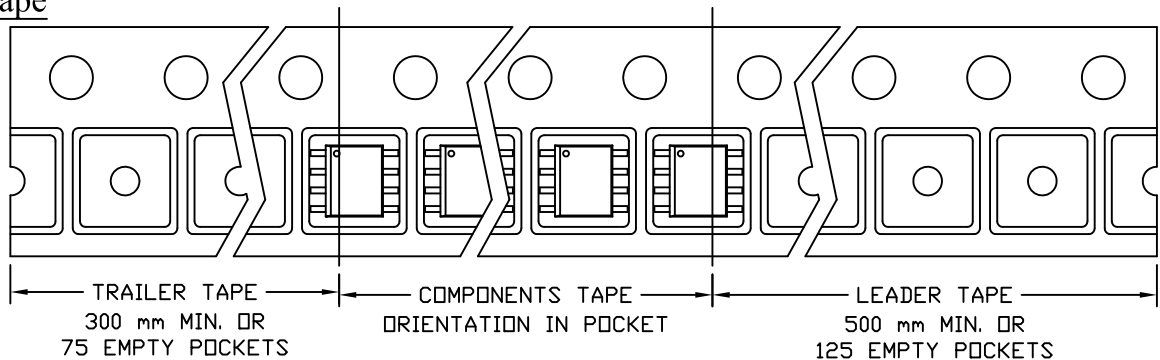
UNIT: MM

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	ø330	ø330.00 ±0.50	ø97.00 ±0.10	13.00 ±0.30	17.40 ±1.00	ø13.00 +0.50 -0.20	10.60	2.00 ±0.50	---	---	---

**SO8/SO8 EP Tape**

Leader / Trailer  
& Orientation

Unit Per Reel:  
3000pcs





# ***AOS Semiconductor Product Reliability Report***

**AO4413,** rev E

**Plastic Encapsulated Device**

**ALPHA & OMEGA Semiconductor, Inc**

**[www.aosmd.com](http://www.aosmd.com)**

This AOS product reliability report summarizes the qualification result for AO4413. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AO4413 passes AOS quality and reliability requirements. The released product will be categorized by the process family and be monitored on a quarterly basis for continuously improving the product quality.

## Table of Contents:

- I. Product Description
- II. Package and Die information
- III. Environmental Stress Test Summary and Result
- IV. Reliability Evaluation

## I. Product Description:

The AO4413 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , and ultra-low low gate charge with a 25V gate rating. This device is suitable for use as a load switch or in PWM applications.

- RoHS Compliant
- Halogen Free

Detailed information refers to datasheet.

## II. Die / Package Information:

	<b>AO4413</b>
<b>Process</b>	Standard sub-micron 30V P-Channel MOSFET
<b>Package Type</b>	SO8
<b>Lead Frame</b>	Cu
<b>Die Attach</b>	Ag epoxy
<b>Bonding</b>	Cu wire
<b>Mold Material</b>	Epoxy resin with silica filler
<b>MSL (moisture sensitive level)</b>	Level 1 based on J-STD-020
<b>Note</b>	* based on information provided by assembler and mold compound supplier

### III. Result of Reliability Stress for AO4413

Test Item	Test Condition	Time Point	Lot Attribution	Total Sample size	Number of Failures	Standard
MSL Precondition	168hr 85°C /85%RH +3 cycle reflow@260°C	-	33 lots	5489pcs	0	JESD22-A113
HTGB	Temp = 150 °c, Vgs=100% of Vgsmax	168hrs 500 hrs 1000 hrs	8 lot 5 lot (Note A*)	1001pcs  77pcs / lot	0	JESD22-A108
HTRB	Temp = 150 °c, Vds=80% of Vdsmax	168hrs 500 hrs 1000 hrs	8 lot 5 lot (Note A*)	1001pcs  77pcs / lot	0	JESD22-A108
HAST	130°C, 85%RH, 33.3 psi, Vgs = 100% of Vgs max	96 hrs	20 lots  (Note A*)	1100pcs  55 pcs / lot	0	JESD22-A110
Pressure Pot	121°C, 29.7psi, RH=100%	96 hrs	24lots  (Note A*)	1848pcs  77 pcs / lot	0	JESD22-A102
Temperature Cycle	-65°C to 150°C, air to air	250 / 500 cycles	33 lots  (Note A*)	2541pcs  77 pcs / lot	0	JESD22-A104

**Note A:** The reliability data presents total of available generic data up to the published date.

### IV. Reliability Evaluation

**FIT rate (per billion): 3**  
**MTTF = 44613 years**

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the selected product (AO4413). Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

$$\text{Failure Rate} = \text{Chi}^2 \times 10^9 / [2 (N) (H) (Af)]$$

$$= 1.83 \times 10^9 / [2 \times (16 \times 77 \times 500 + 10 \times 77 \times 1000) \times 258] = 3$$

$$\text{MTTF} = 10^9 / \text{FIT} = 3.91 \times 10^8 \text{hrs} = 44613 \text{ years}$$

**Chi<sup>2</sup>** = Chi Squared Distribution, determined by the number of failures and confidence interval

**N** = Total Number of units from HTRB and HTGB tests

**H** = Duration of HTRB/HTGB testing

**Af** = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)

Acceleration Factor [Af] =  $\text{Exp} [Ea / k (1/Tj u - 1/Tj s)]$

**Acceleration Factor ratio list:**

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	258	87	32	13	5.64	2.59	1

**Tj s** = Stressed junction temperature in degree (Kelvin), K = C+273.16

**Tj u** = The use junction temperature in degree (Kelvin), K = C+273.16

**K** = Boltzmann's constant, 8.617164 X 10<sup>-5</sup>eV / K

单击下面可查看定价，库存，交付和生命周期等信息

[>>AOS\(万代\)](#)